

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

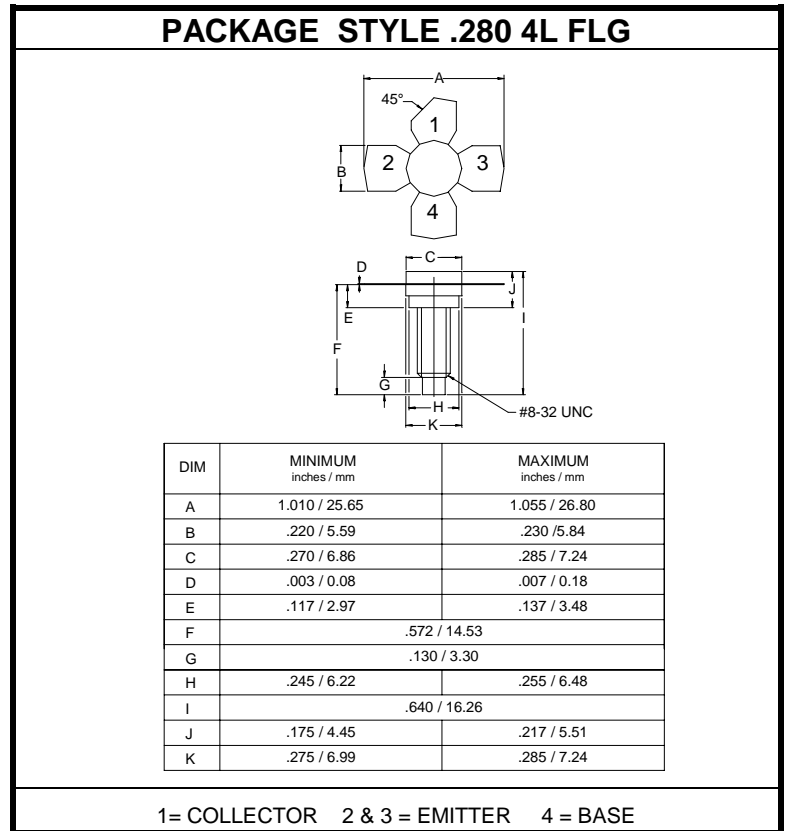
The **ASI MRF654** is Designed for 12.5 V UHF amplifier applications up to 512 MHz.

FEATURES:

- Internal Input Matching Network
- $P_G = 7.8$ dB at 15 W/512 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	3.4 A
V_{CBO}	36 V
V_{CEO}	16 V
V_{EBO}	4.0 V
P_{DISS}	37.75 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	4.6 °C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	16			V
BV_{CES}	$I_C = 50$ mA	36			V
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
I_{CES}	$V_{CE} = 15$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	20		120	---
C_{ob}	$V_{CB} = 12.5$ V $f = 1.0$ MHz			50	pF
P_G η_C	$V_{CE} = 12.5$ V $P_{OUT} = 15$ W $f = 512$ MHz	7.8 50			dB %